

ABSTRACT

The objective of the invention is to provide a ceramic substrate: wherein even if rapid temperature rising or rapid
5 temperature falling is conducted, no problem of cracking or warp of the ceramic substrate occurs; wherein, in case that the ceramic substrate is a ceramic substrate constituting an electrostatic chuck, local dispersion of chuck power is eliminated, in case
10 that the ceramic substrate is a ceramic substrate constituting a hot plate, local dispersion of temperature of a wafer treating face is eliminated, in case that the ceramic substrate is a ceramic substrate constituting a wafer prober, dispersion of applied voltage of a guard electrode or a ground electrode is eliminated and a stray capacitor or noise can be eliminated. The ceramic
15 substrate of the present invention is a ceramic substrate provided with a conductor layer on the surface of the ceramic substrate or inside the ceramic substrate, wherein: the ratio (t_2/t_1) of the average thickness of the conductor layer (t_2) to the average thickness of the ceramic substrate (t_1) is less than
20 0.1 and; a dispersion of the thickness of the conductor layer to the average thickness of the conductor layer is in a range of -70 to +150%.